

3W 1064nm Bare Laser Chip

The chip also uses new epitaxial structure design and material epitaxy, leading cavity surface passivation technology, advanced non-pumped window design and preparation technology, and dry and wet etching combined with self-aligning technology to control the consistency of strip width. In particular, the high yield rate under mass production is guaranteed, and the cost of laser chips is reduced.

Data Sheet:

Item No:LC1064SE3

Item Name:3W 1064nm Bare Laser Chip

Parameters	Min	Typ	Max
Output Power	3W		
Center Wavelength		1064nm	
Spectral Width(FWHM)		10nm	
Fast-Axis Divergence(FWHM)		29	
Slow-Axis Divergence(FWHM)		10	
Wavelength shift vs. Temperature		0.28nm/°C	
Emitter Size		96μm	
Threshold Current		0.35A	
Operating Current		8.0A	9.0A
Operating Voltage		1.4V	1.6V
Power Conversion Efficiency		19%	
Slop Efficiency		0.25W/A	
Operating Temperature	15°C		55°C

